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ST	ORMATION DISCLOSURE ATEMENT BY APPLICANT e several sheets if necessary)	APPLICANT Steven Gerard Mayorga, et al.	
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EXAM- INER INITIAL				DOCU	MENT I	NUMBE	R ·		DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPRO- PRIATE
	- 7	5	0	2	8	5	6	6	7/2/91	Andre Lagendijk	437	238	7/27/90
		5	5	4	8	0	0	6	8/20/96	Satao Hirabayashi, et al	524	82	11/17/94
		5.	3	8	0	8	1	2	1/10/95	Michael A. Lutz, et al	-528	15	1/10/94
		3	3	4	4	1	1	1	9/26/67	Alan J. Chalk	260	46.5	9/26/66
		3	8	8	2	0	8	3	5/6/75	Abe Berger, et al	260	46.5	11/21/73
		3	9	9	8	8	6	5	12/21/76	George Siciliano, et al	260	448.2	3/12/75
		2	8	3	7	5	5	0	6/3/58	Maurice Prober	260	448.2	5/18/55
		6	3	6	8	3	5	9	4/9/02	R.J. Perry, et al	8	142	12/17/99
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## **FOREIGN PATENT DOCUMENTS**

	DOCUMENT NUMBER								COUNTRY	CLASS	SUBCLASS .	TRANSI	LATION
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	7_	1	4	5	1	7	9	8/25/99	JP	C07F	7/21	X	
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	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)  "User's Guide For: Glass Deposition With Teos," Dr. Arthur K. Hochberg, Schumacher, 1992.								
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